Silicon NPN Power Transistors 2SC4466

DESCRIPTION

- With TO-3PN package
- Complement to type 2SA1693

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

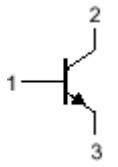

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	120	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
I_B	Base current		3	A
P_C	Collector power dissipation	T_C=25℃	60	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA ;I_B=0	80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2A; I_B=0.2A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=120V; I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			10	μA
h_{FE}	DC current gain	I_C=2A ; V_{CE}=4V	50		180	
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=10V,f=1MHz		110		pF
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=12V		20		MHz

Switching times

t_{on}	Turn-on time	I_C=3A;R_L=10Ω I_{B1}=- I_{B2}=0.3A V_{CC}=30V		0.16		μs
t_s	Storage time			2.60		μs
t_f	Fall time			0.34		μs

◆ **h_{FE} Classifications**

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE

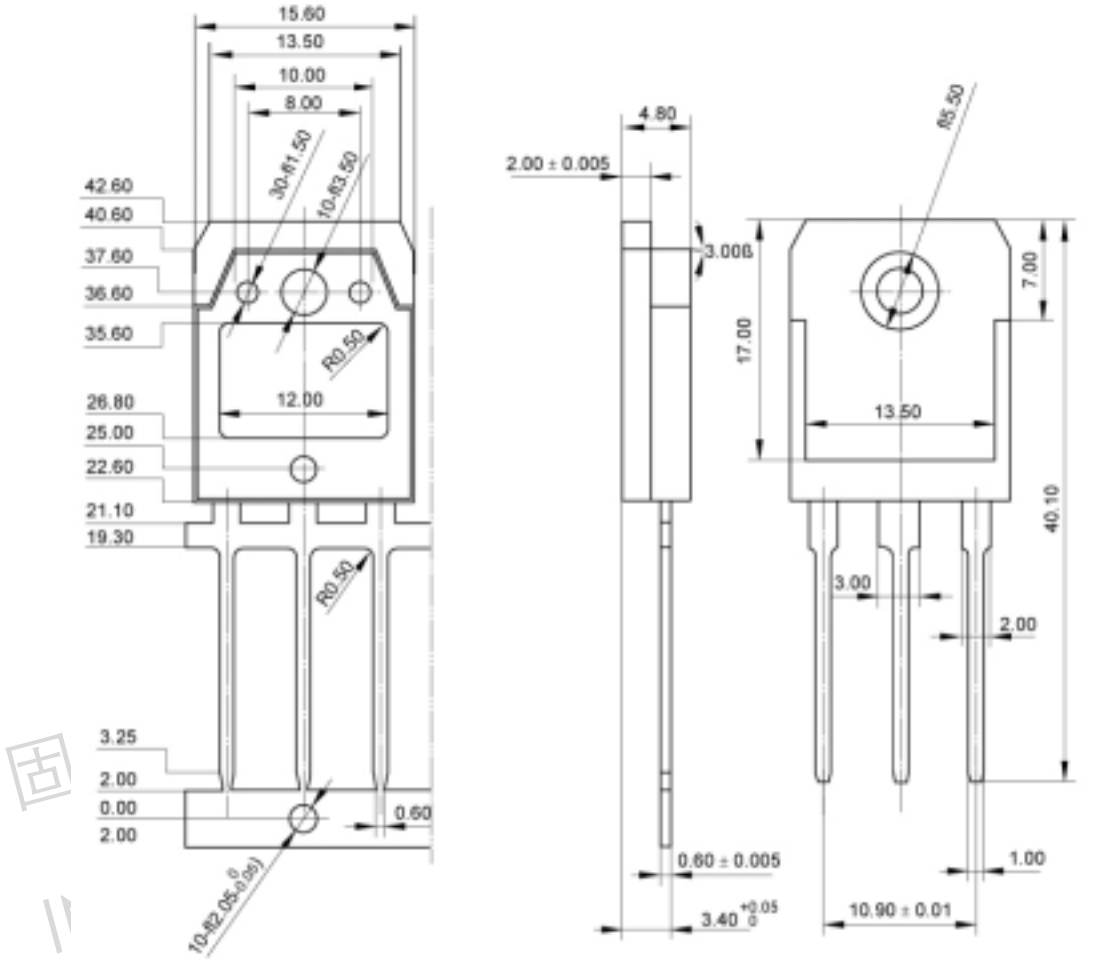

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

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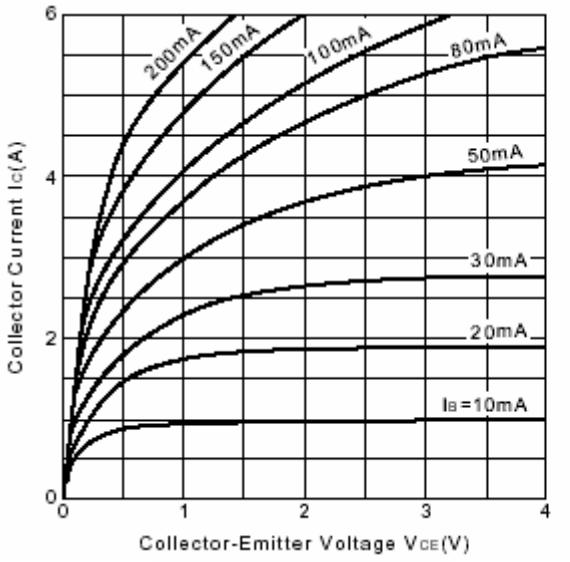

Fig.3 Static Characteristic

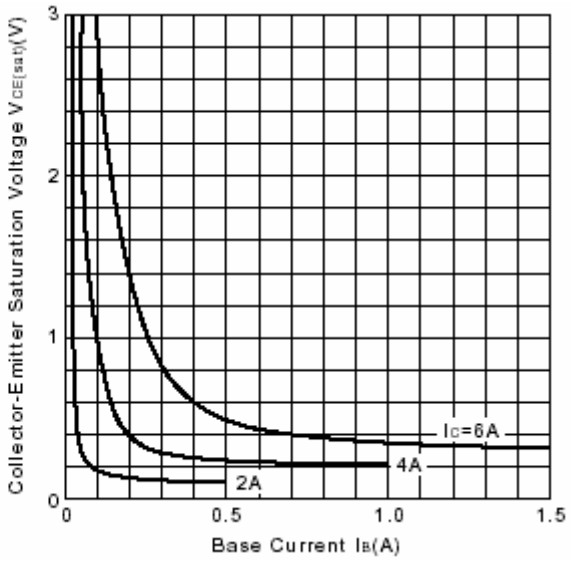

Fig.4 $V_{CE}(sat)-I_B$ Characteristics

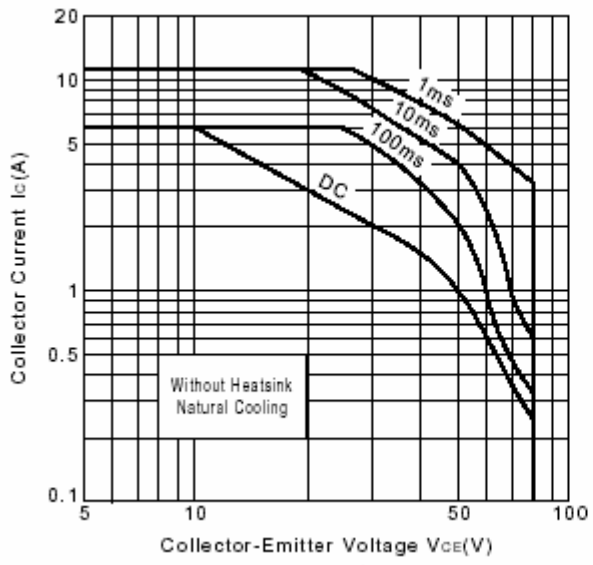

Fig.5 Safe Operating Area

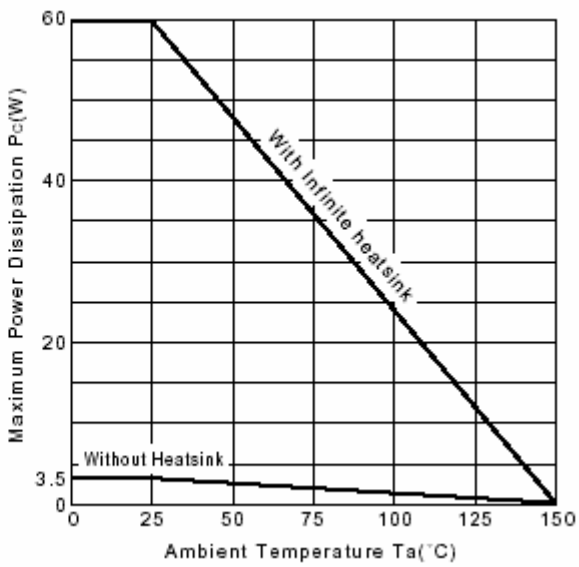

Fig.6 Pc-Ta Derating

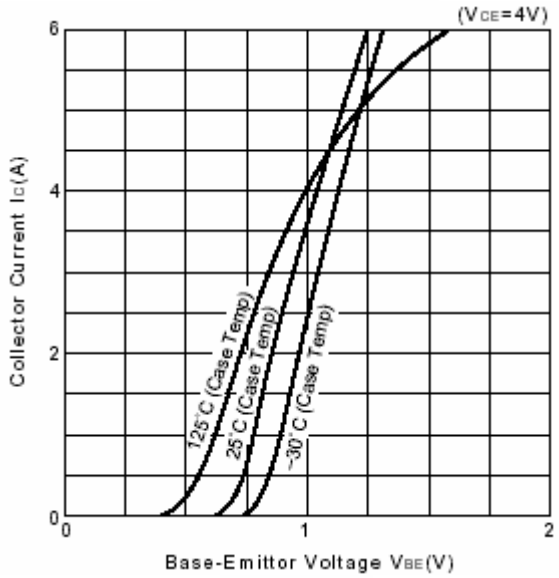

Fig.7 I_C-V_{BE}

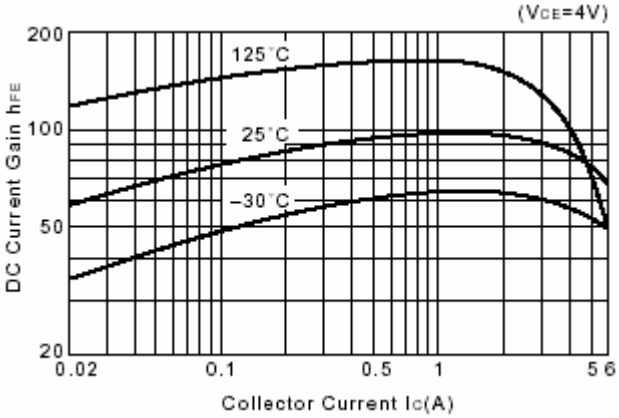

Fig.8 DC current Gain